

# Abstracts

## Highly Producible Monolithic Q-Band MESFET VCO

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*S. Martin, S. Meyer, E. Reese and K. Salzman. "Highly Producible Monolithic Q-Band MESFET VCO." 1992 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 92.1 (1992 [MCS]): 57-60.*

A fully monolithic self-biased VCO has been demonstrated at 40 GHz. A buffer amplifier, all bias elements, and a tuning varactor have been integrated on a 4.4- x 2.0-mm chip. Gate lengths of 0.35  $\mu$ m were used in for this FET based oscillator that delivers greater than 90 mW of output power over a tuning bandwidth of 2.8 GHz.

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